



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Re the Application of

Kazuo ICHIKAWA et al.

Group Art Unit: 1763

Application No.: 09/670,877

Examiner: R. Zervigon

Filed: September 27, 2000

Docket No.: 107469

For: CVD SUBSTRATE AND CLEANING METHOD

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**LARGE ENTITY REQUEST FOR
CONTINUED EXAMINATION UNDER 37 C.F.R. §1.114**

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. §1.114, Applicants hereby request continued examination and entry and consideration of the attached submission. The above-identified application was filed on or after June 8, 1995. Thus, entry is proper under 37 C.F.R. §1.114(d).

Attached hereto is our check no. 138755 in the amount of ☒ \$750.00 as payment of the fees set forth in 37 C.F.R. §1.17(e). The Director is hereby authorized to charge any additional fees or credit any overpayment associated with this communication to Deposit Account No. 15-0461. Two duplicate copies of this page are enclosed.

Respectfully submitted,


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02 FC:1801 750.00 OP

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JAO:SXT/amw

Date: February 6, 2003

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PATENT APPLICATION

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copy #7

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AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the August 6, 2002 Office Action and in conjunction with the Request for Continued Examination filed herewith, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 3 as follows:

1. (Amended) A CVD system provided with a plasma generator having a plasma generation chamber separated from a film deposition chamber in which a substrate is arranged, wherein a material gas is directly supplied into the film deposition chamber, radicals in the plasma are introduced into the film deposition chamber from the plasma generator through introduction holes of a lower plate, and a thin film is deposited on the substrate, said CVD system further comprising:
 - a cleaning gas feeder provided to said plasma generator,
 - said lower plate is connected to ground, and
 - each of said introduction holes is designed to pass the radicals only to the film deposition chamber.